

Silicon NPN Power Transistors**2N5598 2N5600 2N5602 2N5604****DESCRIPTION**

- With TO-66 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For high frequency power amplifier ; audio power amplifier and drivers.

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Fig.1 simplified outline (TO-66) and symbol****Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N5598	Open emitter	80	V
		2N5600/5602		100	
		2N5604		120	
V _{CEO}	Collector-emitter voltage	2N5598	Open base	60	V
		2N5600/5602		80	
		2N5604		100	
V _{EBO}	Emitter-base voltage		Open collector	5	V
I _C	Collector current			2	A
P _D	Total power dissipation		T _C =25□	20	W
T _j	Junction temperature			150	□
T _{stg}	Storage temperature			-65~150	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	4.37	□/W

Silicon NPN Power Transistors**2N5598 2N5600 2N5602 2N5604****CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(SUS)}$	Collector-emitter sustaining voltage	2N5598	$I_C=50mA; I_B=0$	60			V
		2N5600/5602		80			
		2N5604		100			
V_{CEsat}	Collector-emitter saturation voltage		$I_C=1A; I_B=0.1A$			1.0	V
V_{BE}	Base-emitter on voltage		$I_C=1A; V_{CE}=5V$			1.5	V
I_{CBO}	Collector cut-off current		$V_{CB}=\text{Rated } V_{CBO}; I_E=0$			0.1	mA
I_{CEO}	Collector cut-off current		$V_{CE}=\text{Rated } V_{CEO}; I_B=0$			1.0	mA
I_{EBO}	Emitter cut-off current		$V_{EB}=5V; I_C=0$			0.1	mA
h_{FE}	DC current gain	2N5598/5602	$I_C=1A; V_{CE}=5V$	70		200	
		2N5600/5604		30		90	
f_T	Transition frequency	2N5598/5602	$I_C=0.5A; V_{CE}=10V$	60			MHz
		2N5600/5604		50			

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PACKAGE OUTLINE

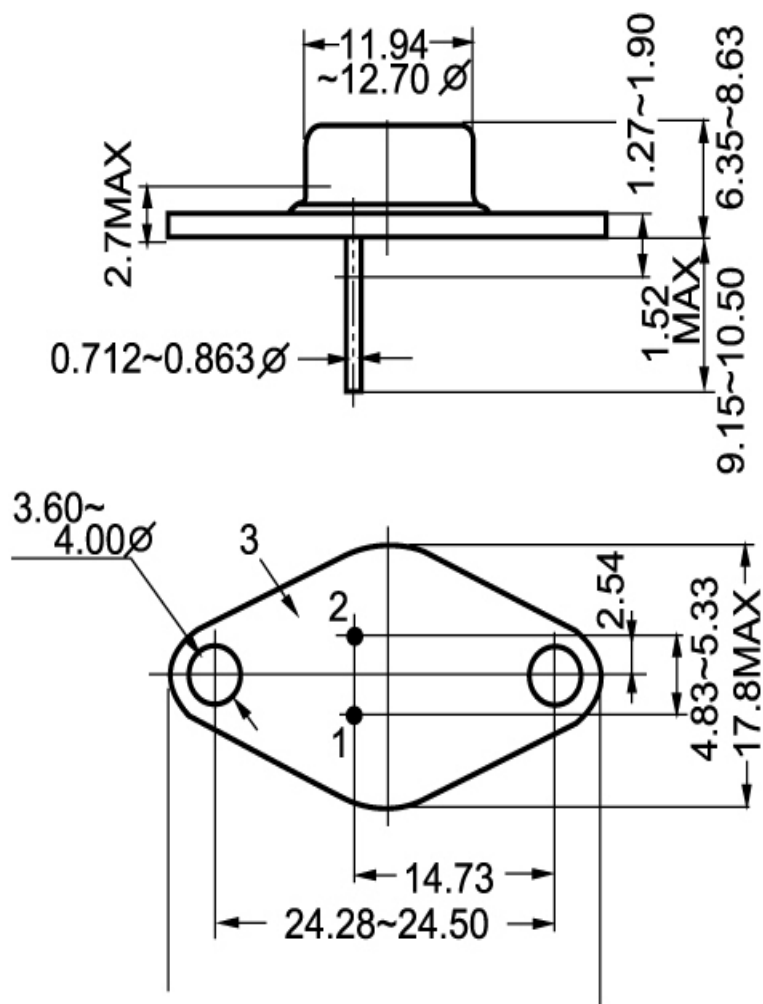


Fig.2 outline dimensions